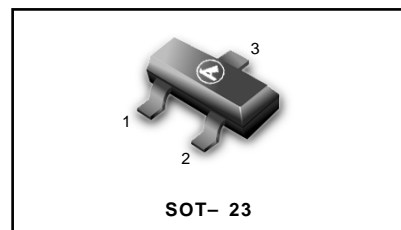


High Voltage Switching Diode

FEATURE

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LBAS21SLT1G
S-LBAS21SLT1G

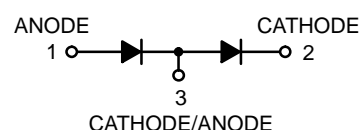


DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAS21SLT1G S-LBAS21SLT1G	JT	3000/Tape&Reel
LBAS21SLT3G S-LBAS21SLT3G	JT	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	250	Vdc
Peak Forward Current	I_F	225	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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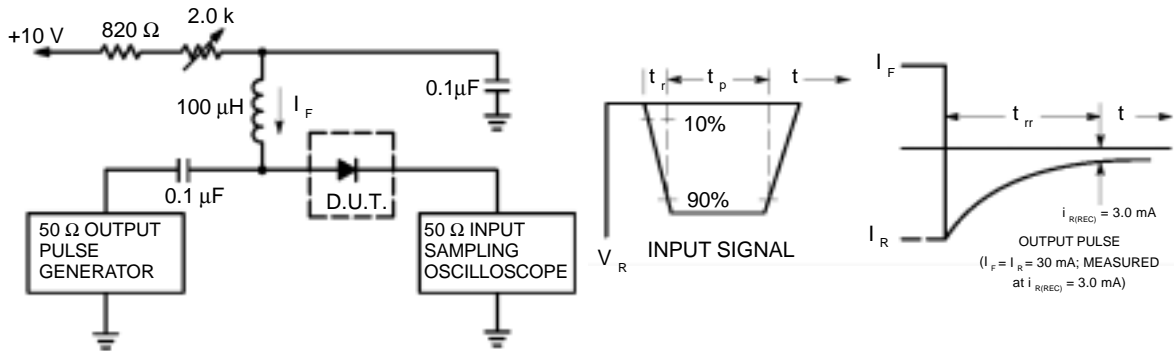
OFF CHARACTERISTICS

Reverse Voltage Leakage Current ($V_R = 200\text{Vdc}$) ($V_R = 200\text{Vdc}, T_J = 150^\circ\text{C}$)	I_R	—	0.1 100	μAdc
Reverse Breakdown Voltage ($I_{BR} = 100 \mu\text{Adc}$)	$V_{(BR)}$	250	—	Vdc
Forward Voltage ($I_F = 100 \text{mAdc}$) ($I_F = 200 \text{mAdc}$)	V_F	—	1000 1250	mV
Diode Capacitance ($V_R = 0, f = 1.0 \text{MHz}$)	C_D	—	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30\text{mAdc}, R_L = 100 \Omega$)	t_{rr}	—	50	ns

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

LBAS21SLT1G, S-LBAS21SLT1G



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
- 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
- 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

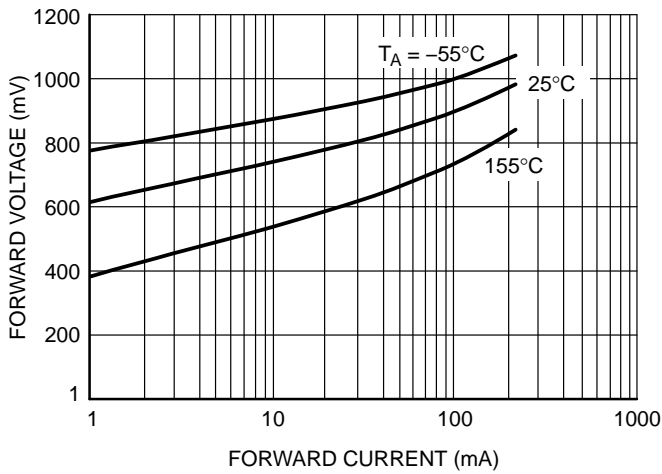


Figure 2. Forward Voltage

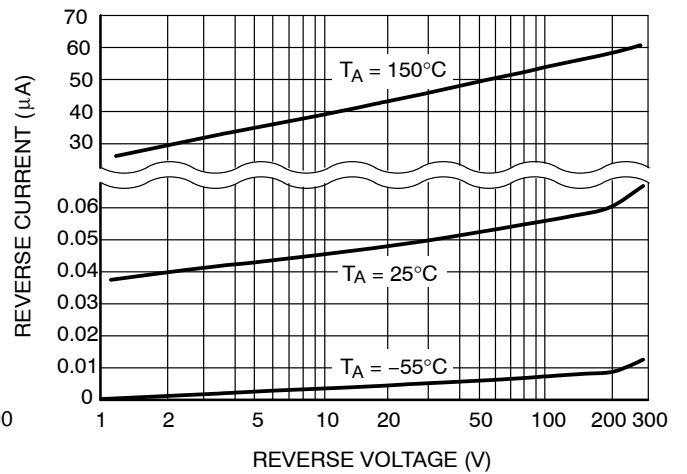
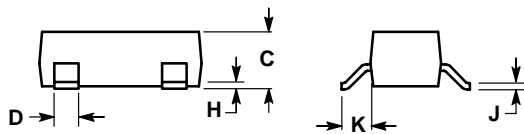
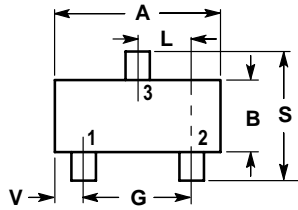


Figure 3. Reverse Leakage

LBAS21SLT1G, S-LBAS21SLT1G

SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

